

Guangdong Yuejing High Technology CO.,LTD.

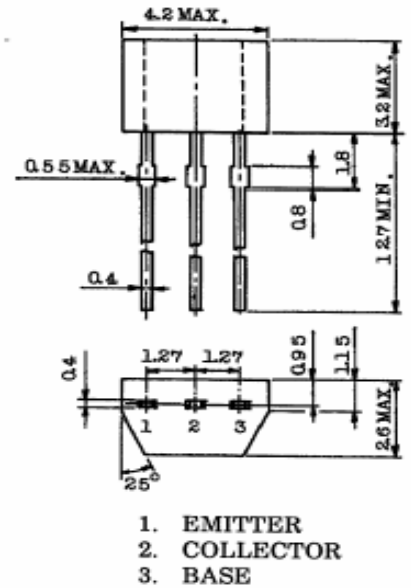
RN1204

—NPN silicon—

■■ APPLICATION: Interface Circuit and Driver Circuit Applications.

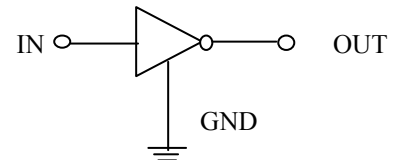
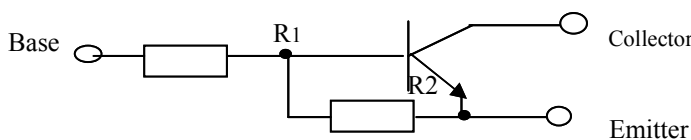
■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	10	V
Collector current	I _C	100	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	80				V _{CE} = 5V, I _C = 10mA
Collector Cut-off Current	I _{CBO}			0.1	μA	V _{CB} = 50V, I _E =0
Collector-Emitter Cut-off Current	I _{CEO}			0.5	μA	V _{CB} = 50V, I _E =0
Emitter Cut-off Current	I _{EBO}	0.082		0.15	mA	V _{EB} = 10V, I _C =0
Input Voltage (ON)	V _{I(ON)}	1.5		5	V	V _{CE} = 0.2V, I _C = 5mA
Output Voltage (OFF)	V _{I(OFF)}	1		1.5	V	V _{CE} = 5V, I _C = 0.1mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.1	0.3	V	I _C = 5mA, I _B = 0.25mA
Gain bandwidth product	f _T	100	250		MHz	I _C = 5mA, V _{CE} = 10V
Base Resistance	R ₁	32.9	47	61.1	KΩ	
Emitter Resistance	R ₂	32.9	47	61.1	KΩ	
Common Base Output Capacitance	C _{ob}		3	6	pF	V _{CB} = 10V, I _E =0, f = 1MHz



■■ h_{FE} Classification And Marking

Print Mark **XD**

Classification

h_{FE} **≥ 80**